

-20V P-Channel Enhancement Mode MOSFET

General Features

- $V_{DS} = -20V, I_D = -4A$
 $R_{DS(ON)} < 63m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 55m\Omega @ V_{GS} = -4.5V$
 ESD Rating: 2500V HBM
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

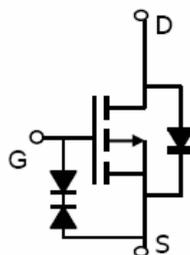
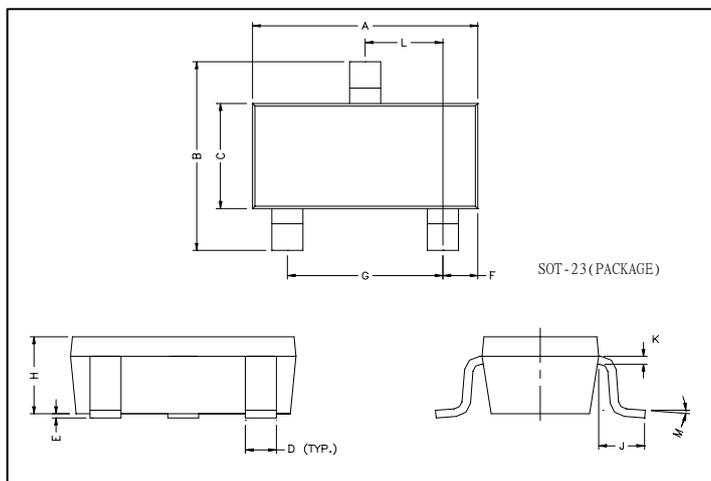
Application

- PWM application
- Load switch

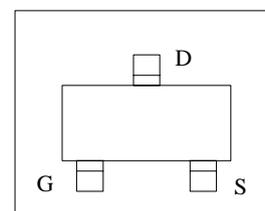
Description

The AO3415 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

Package Dimensions



Schematic diagram



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 2.70 | 3.10 | G | 1.90 | REF. |
| B | 2.40 | 2.80 | H | 1.00 | 1.30 |
| C | 1.40 | 1.60 | K | 0.10 | 0.20 |
| D | 0.35 | 0.50 | J | 0.40 | - |
| E | 0 | 0.10 | L | 0.85 | 1.15 |
| F | 0.45 | 0.55 | M | 0° | 10° |

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate-Source Voltage | V_{GS} | ±8 | V |
| Drain Current-Continuous | I_D | -4 | A |
| Drain Current-Pulsed (Note 1) | I_{DM} | -30 | A |
| Maximum Power Dissipation | P_D | 1.4 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | °C |

Thermal Characteristic

| | | | |
|--|-----------------|------|------|
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 89.3 | °C/W |
|--|-----------------|------|------|

Electrical Characteristics (TA=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|--------------------------------|------------|--------------------------------|-----|-----|-----|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = -250\mu A$ | -20 | | - | V |

| | | | | | | |
|---|--------------|---|------|-------|----------|-----------|
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=-20V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 8V, V_{DS}=0V$ | - | - | ± 10 | μA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=-250\mu A$ | -0.4 | -0.65 | -1.0 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}=-4.5V, I_D=-4A$ | - | 34. | 55 | $m\Omega$ |
| | | $V_{GS}=-2.5V, I_D=-4A$ | - | 44 | 63 | $m\Omega$ |
| Forward Transconductance | g_{FS} | $V_{DS}=-5V, I_D=-4A$ | 8 | - | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$ | - | 950 | - | PF |
| Output Capacitance | C_{oss} | | - | 165 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 120 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=-10V, R_L=2.5\Omega$ $V_{GS}=-4.5V, R_{GEN}=3\Omega$ | - | 12 | | nS |
| Turn-on Rise Time | t_r | | - | 10 | | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 19 | | nS |
| Turn-Off Fall Time | t_f | | - | 25 | | nS |
| Total Gate Charge | Q_g | $V_{DS}=-10V, I_D=-4A,$ $V_{GS}=-4.5V$ | - | 12 | | nC |
| Gate-Source Charge | Q_{gs} | | - | 1.4 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 3.6 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | $V_{GS}=0V, I_S=-1A$ | - | - | -1.2 | V |
| Diode Forward Current (Note 2) | I_S | | - | - | -2.2 | A |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

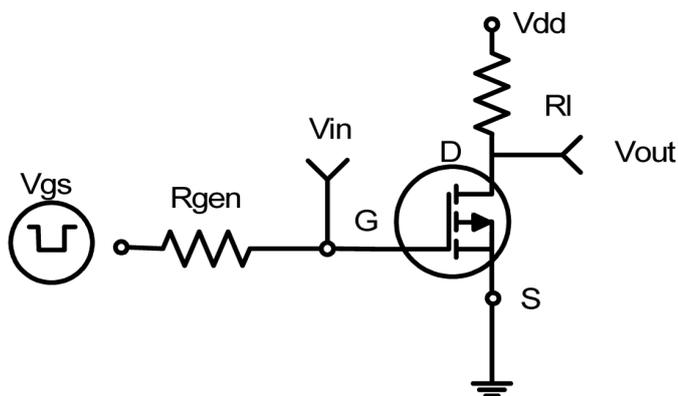


Figure 1: Switching Test Circuit

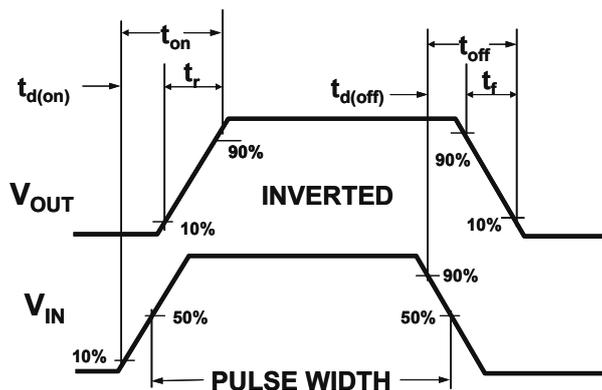


Figure 2: Switching Waveforms

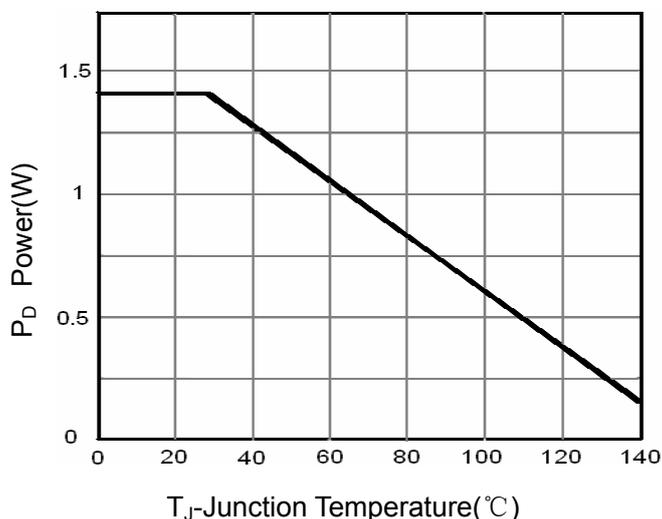


Figure 3 Power Dissipation

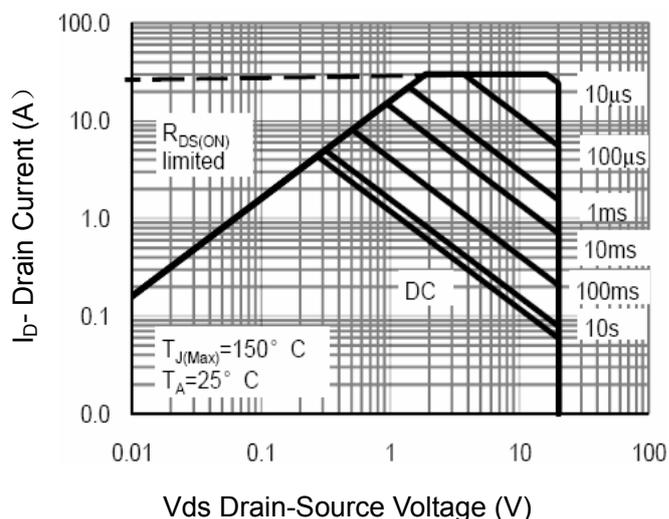


Figure 4 Safe Operation Area

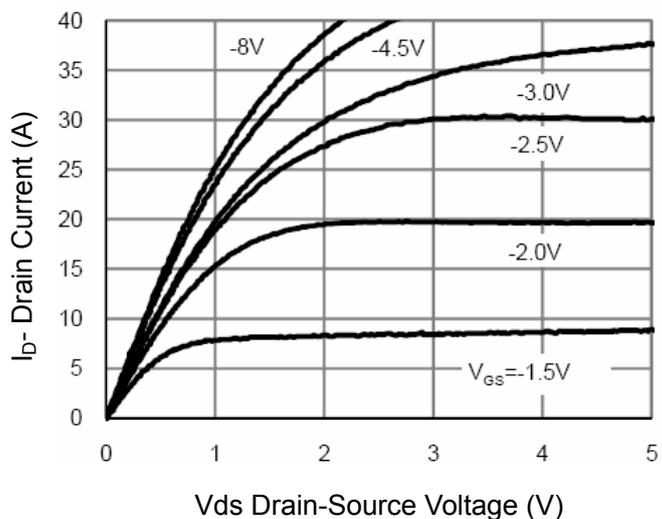


Figure 5 Output CHARACTERISTICS

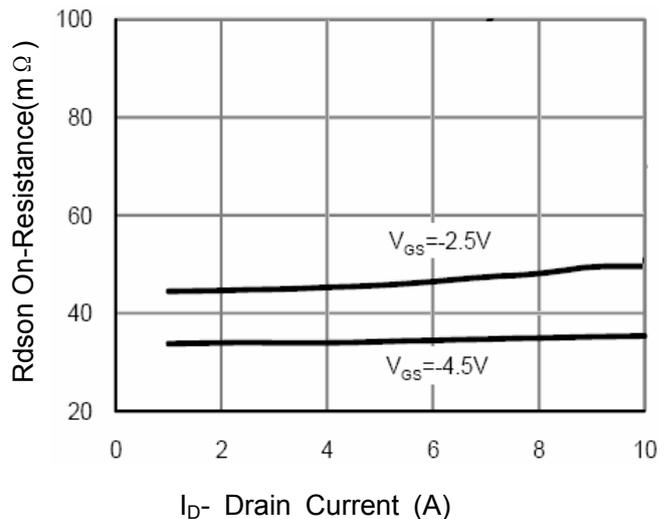


Figure 6 Drain-Source On-Resistance

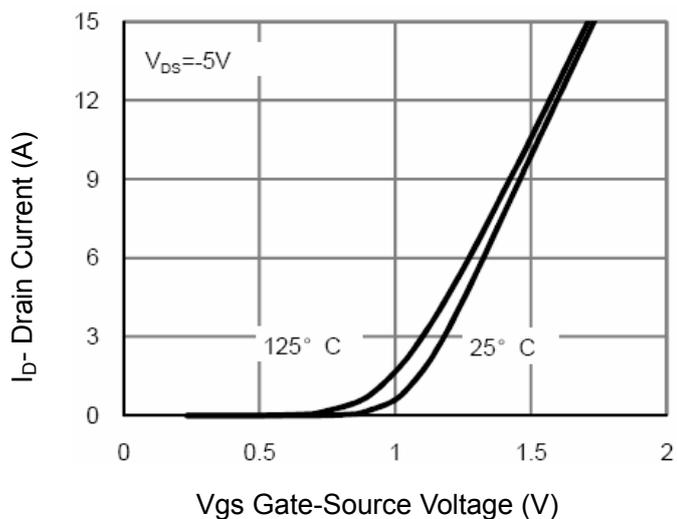


Figure 7 Transfer Characteristics

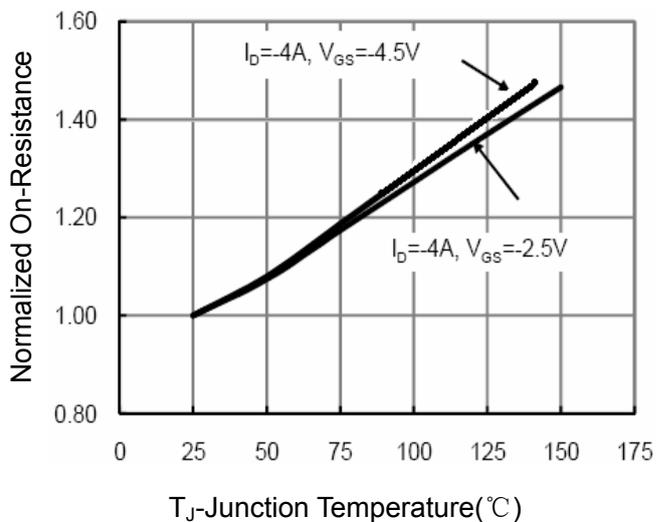


Figure 8 Drain-Source On-Resistance

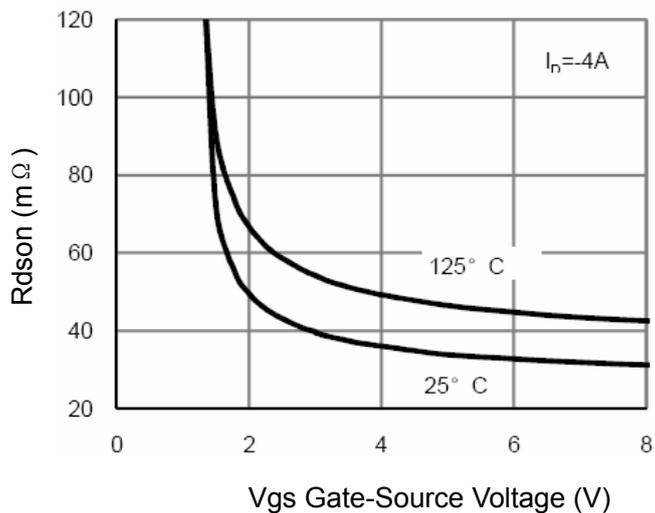


Figure 9 $R_{DS(on)}$ vs V_{GS}

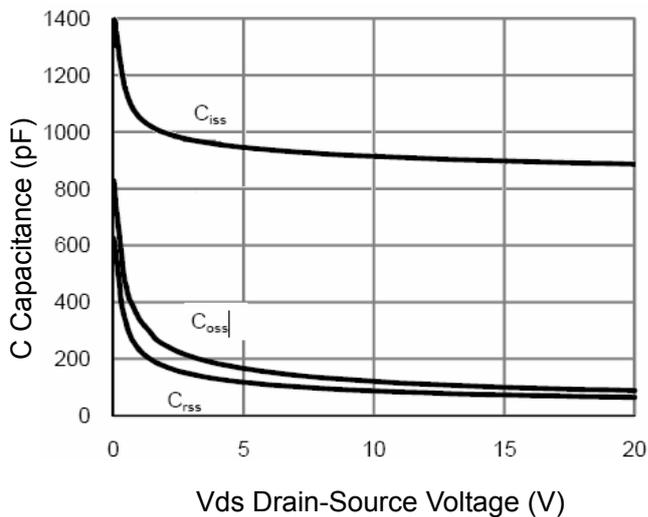


Figure 10 Capacitance vs V_{DS}

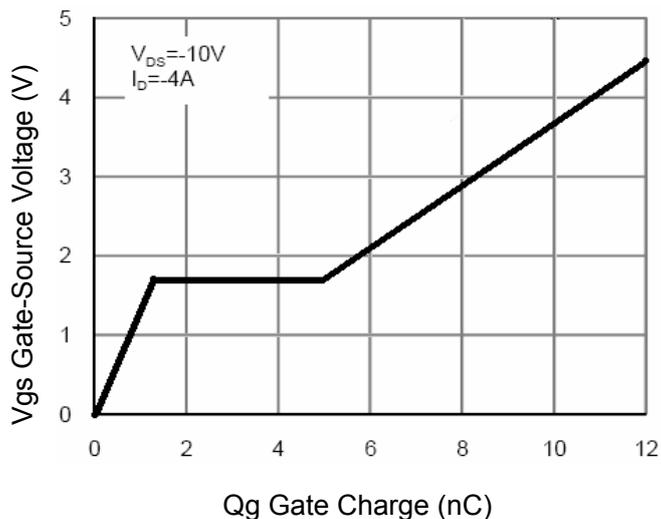


Figure 11 Gate Charge

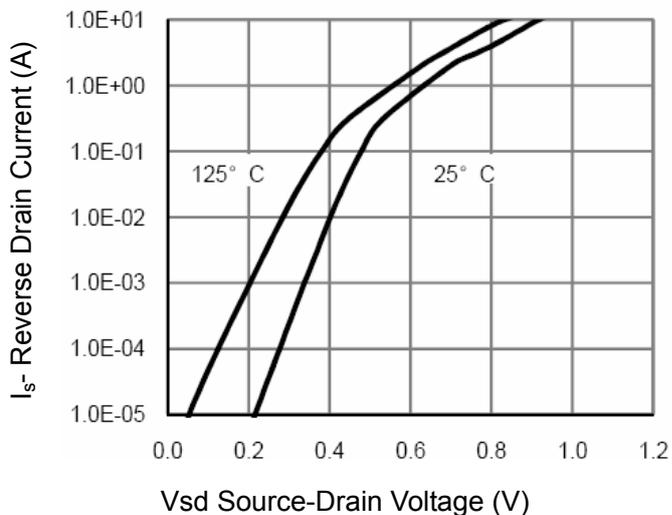


Figure 12 Source- Drain Diode Forward

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